

1. Record Nr.	UNINA9910143584503321
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Titolo	Design and characterization of integrated varactors for RF applications [[electronic resource] /] / Inigo Gutierrez, Juan Melendez, Erik Hernandez
Pubbl/distr/stampa	Chichester, West Sussex, England ; ; Hoboken, NJ, : Wiley, c2006
ISBN	1-280-85476-6 9786610854769 0-470-03592-7 1-60119-377-7 0-470-03591-9
Descrizione fisica	1 online resource (182 p.)
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Disciplina	621.3815 621.381522
Soggetti	Varactors - Design and construction Radio capacitors - Design and construction Radio circuits - Design and construction Integrated circuits - Design and construction Electronic books.
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia
Note generali	Description based upon print version of record.
Nota di bibliografia	Includes bibliographical references and index.
Nota di contenuto	Design and Characterization of Integrated Varactors for RF Applications; Contents; List of Figures; List of Tables; Preface; Acknowledgements; 1 Introduction; 1.1 Passive Elements; 1.2 Figures of Merit of Varactors; 1.2.1 Quality Factor; 1.2.2 Tuning Range; 1.2.3 Self-resonant Frequency(fr); 1.2.4 Effective Silicon Area; 1.2.5 Absolute Capacity Value; 1.3 Principal Types of Varactor Manufacture; 1.3.1 Discrete Varactors; 1.3.2 MEMS Varactors; 1.3.3 BST Varactors; 1.3.4 Integrated Varactors using Standard Technologies; References; 2 PN-junction Varactors 2.1 The Operating Principle of a PN-junction Varactor2.1.1 Electrical Phenomena in a PN-junction Varactor; 2.2 Different Architectures of

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Sommario/riassunto

Varactors are passive semiconductor devices used in electronic circuits, as a voltage-controlled way of storing energy in order to boost the amount of electric charge produced. In the past, the use of low-cost fabrication processes such as complementary metal oxide semiconductor (CMOS) and silicon germanium (SiGe) were kept for integrated circuits working in frequency ranges below the GHz. Now, the increased working frequency of radio frequency integrated circuits (RF ICs) for communication devices, and the trend of system-on-chip technology, has pushed the requirements of varactors to the lim
